

TECHNICAL SPECIFICATION

**Nanomanufacturing - Key control characteristics -
Part 6-28: Graphene-related products - Number of layers for graphene films on a
substrate: Raman spectroscopy**

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IEC Secretariat
3, rue de Varembe
CH-1211 Geneva 20
Switzerland

Tel.: +41 22 919 02 11
info@iec.ch
www.iec.ch

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**Nanomanufacturing -
Key control characteristics -
Part 6-28: Graphene-related products -
Number of layers for graphene films on a substrate: Raman spectroscopy**

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The text of this Technical Specification is based on the following documents:

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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this Technical Specification is English.